

IHM-B module with Trench/Fieldstop IGBT4 and Emitter Controlled 4 diode

Features

- Electrical features
 - $V_{CES} = 3300\text{ V}$
 - $I_{C\text{nom}} = 2400\text{ A} / I_{CRM} = 4800\text{ A}$
 - High current density
 - High DC stability
 - High short-circuit capability
 - Low switching losses
 - Low V_{CESat}
 - $T_{vj\text{op}} = 150\text{ °C}$
 - Trench IGBT 4
 - Unbeatable robustness
 - V_{CESat} with positive temperature coefficient
 - Low Q_g and C_{res}
- Mechanical features
 - ALSiC base plate for increased thermal cycling capability
 - High power density
 - Isolated base plate
 - Package with CTI > 600
 - RoHS compliant



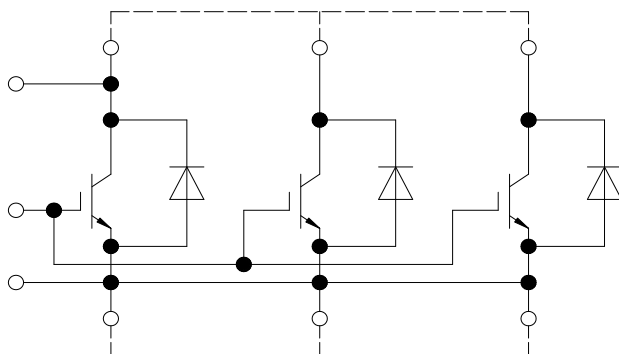
Potential applications

- High power converters
- Medium voltage converters
- Motor drives
- Traction drives
- UPS systems
- Active frontend (energy recovery)
- Commercial Agriculture Vehicles

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description



external connection
(to be done)

Table of contents

	Description	1
	Features	1
	Potential applications	1
	Product validation	1
	Table of contents	2
1	Package	3
2	IGBT, Inverter	3
3	Diode, Inverter	5
4	Characteristics diagrams	7
5	Circuit diagram	11
6	Package outlines	11
	Disclaimer	12

1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50$ Hz	6.0	kV
Partial discharge extinction voltage	V_{isol}	RMS, $f = 50$ Hz, $Q_{PD} \leq 10$ pC	2.6	kV
DC stability	$V_{CE(D)}$	$T_{vj}=25^{\circ}C$, 100 Fit	2100	V
Material of module baseplate			AlSiC	
Creepage distance	d_{Creep}	terminal to heatsink	32.2	mm
Clearance	d_{Clear}	terminal to heatsink	19.1	mm
Comparative tracking index	CTI		> 600	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Stray inductance module	L_{SCE}			6		nH	
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_C=25^{\circ}C$, per switch		0.08		mΩ	
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C=25^{\circ}C$, per switch		0.095		mΩ	
Storage temperature	T_{stg}		-40		150	°C	
Mounting torque for modul mounting	M	- Mounting according to valid application note	M6, Screw	4.25		5.75	Nm
Terminal connection torque	M	- Mounting according to valid application note	M4, Screw	1.8		2.1	Nm
			M8, Screw	8		10	
Weight	G			1200		g	

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Collector-emitter voltage	V_{CES}		$T_{vj} = -40^{\circ}C$	3300	V
			$T_{vj} = 150^{\circ}C$	3300	
Continous DC collector current	I_{CDC}	$T_{vj\ max} = 150^{\circ}C$	$T_C = 105^{\circ}C$	2400	A
Repetitive peak collector current	I_{CRM}	$t_p = 1$ ms		4800	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 2400\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$	2.40	2.65	V
			$T_{vj} = 125\ ^\circ C$	2.95		
			$T_{vj} = 150\ ^\circ C$	3.10	3.25	
Gate threshold voltage	V_{GEth}	$I_C = 94\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$	5.20	5.80	6.40	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CE} = 1800\ V$		40		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$		0.5		Ω
Input capacitance	C_{ies}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		280		nF
Reverse transfer capacitance	C_{res}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		8		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 3300\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$		5	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$			400	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 2400\ A, V_{CE} = 1800\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.5\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.560		μs
			$T_{vj} = 125\ ^\circ C$	0.660		
			$T_{vj} = 150\ ^\circ C$	0.670		
Rise time (inductive load)	t_r	$I_C = 2400\ A, V_{CE} = 1800\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.5\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.250		μs
			$T_{vj} = 125\ ^\circ C$	0.270		
			$T_{vj} = 150\ ^\circ C$	0.290		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 2400\ A, V_{CE} = 1800\ V, V_{GE} = \pm 15\ V, R_{Goff} = 3.3\ \Omega$	$T_{vj} = 25\ ^\circ C$	4.000		μs
			$T_{vj} = 125\ ^\circ C$	4.300		
			$T_{vj} = 150\ ^\circ C$	4.300		
Fall time (inductive load)	t_f	$I_C = 2400\ A, V_{CE} = 1800\ V, V_{GE} = \pm 15\ V, R_{Goff} = 3.3\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.540		μs
			$T_{vj} = 125\ ^\circ C$	1.180		
			$T_{vj} = 150\ ^\circ C$	1.400		
Turn-on energy loss per pulse	E_{on}	$I_C = 2400\ A, V_{CE} = 1800\ V, L_\sigma = 85\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 0.5\ \Omega, di/dt = 7600\ A/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	2000		mJ
			$T_{vj} = 125\ ^\circ C$	3400		
			$T_{vj} = 150\ ^\circ C$	3900		
Turn-off energy loss per pulse	E_{off}	$I_C = 2400\ A, V_{CE} = 1800\ V, L_\sigma = 85\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 3.3\ \Omega, dv/dt = 1500\ V/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	3500		mJ
			$T_{vj} = 125\ ^\circ C$	4600		
			$T_{vj} = 150\ ^\circ C$	4950		
SC data	I_{SC}	$V_{GE} \leq 15\ V, V_{CC} = 2400\ V, V_{CEmax} = V_{CES} - L_{sCE} * di/dt$	$t_P \leq 10\ \mu s, T_{vj} \leq 150\ ^\circ C$	9600		A
Thermal resistance, junction to case	R_{thJC}	per IGBT			5.50	K/kW

Table 4 Characteristic values (continued)

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, case to heatsink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W/(m}^2\text{K)}$		4.30		K/kW
Temperature under switching conditions	T_{vjop}		-40		150	°C

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = -40 \text{ }^\circ\text{C}$	3300	V
			$T_{vj} = 150 \text{ }^\circ\text{C}$	3300	
Continuous DC forward current	I_F		2400	A	
Repetitive peak forward current	I_{FRM}	$t_P = 1 \text{ ms}$	4800	A	
I^2t - value	I^2t	$t_P = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ }^\circ\text{C}$	1230	kA ² s
			$T_{vj} = 150 \text{ }^\circ\text{C}$	1110	
Maximum power dissipation	P_{RQM}	$T_{vj} = 150 \text{ }^\circ\text{C}$	5400	kW	
Minimum turn-on time	t_{onmin}		10	µs	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	V_F	$I_F = 2400 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		2.90	3.30	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		2.60		
			$T_{vj} = 150 \text{ }^\circ\text{C}$		2.50	2.80	
Peak reverse recovery current	I_{RM}	$V_R = 1800 \text{ V}, I_F = 2400 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 7600 \text{ A}/\mu\text{s} (T_{vj} = 150 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		2440		A
			$T_{vj} = 125 \text{ }^\circ\text{C}$		2820		
			$T_{vj} = 150 \text{ }^\circ\text{C}$		2880		
Recovered charge	Q_r	$V_R = 1800 \text{ V}, I_F = 2400 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 7600 \text{ A}/\mu\text{s} (T_{vj} = 150 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1100		µC
			$T_{vj} = 125 \text{ }^\circ\text{C}$		2100		
			$T_{vj} = 150 \text{ }^\circ\text{C}$		2500		
Reverse recovery energy	E_{rec}	$V_R = 1800 \text{ V}, I_F = 2400 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 7600 \text{ A}/\mu\text{s} (T_{vj} = 150 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1480		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$		2750		
			$T_{vj} = 150 \text{ }^\circ\text{C}$		3200		

Table 6 Characteristic values (continued)

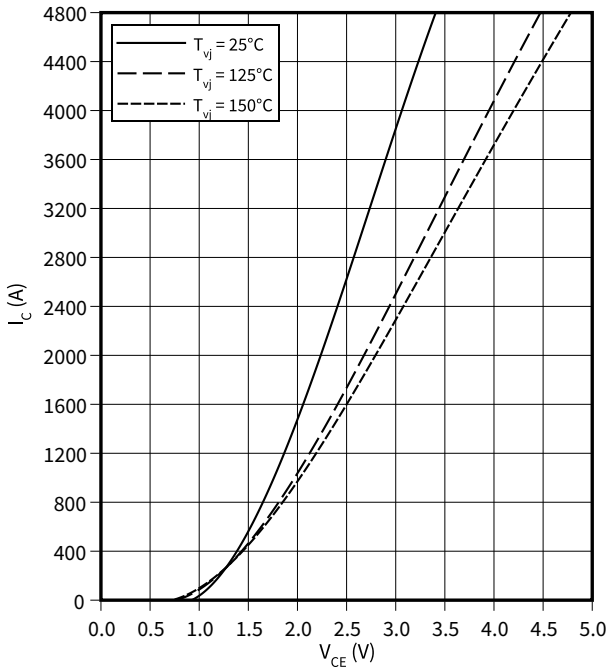
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	R_{thJC}	per diode			10.6	K/kW
Thermal resistance, case to heatsink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W/(m}^2\text{K)}$		5.10		K/kW
Temperature under switching conditions	$T_{vj\ op}$		-40		150	°C

4 Characteristics diagrams

output characteristic (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

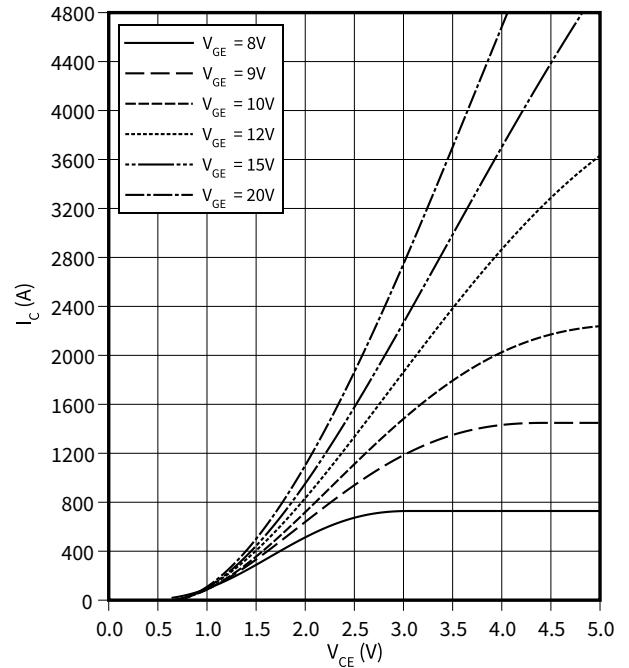
$$V_{GE} = 15 \text{ V}$$



output characteristic (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

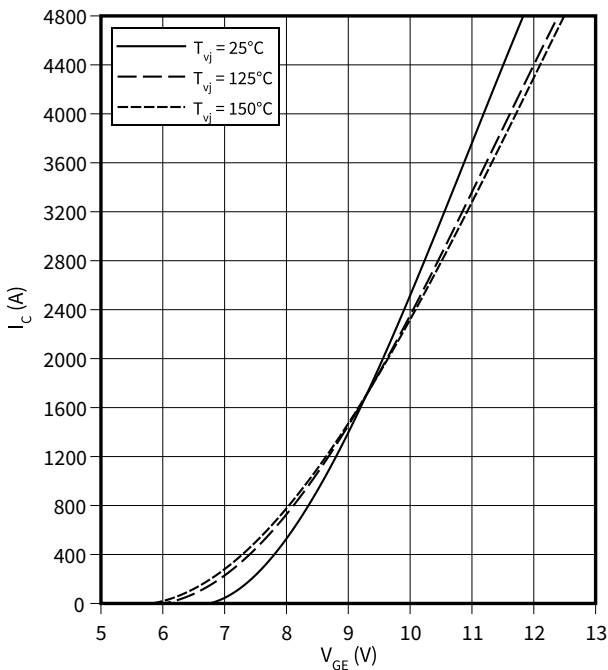
$$T_{vj} = 150 \text{ °C}$$



transfer characteristic (typical), IGBT, Inverter

$$I_C = f(V_{GE})$$

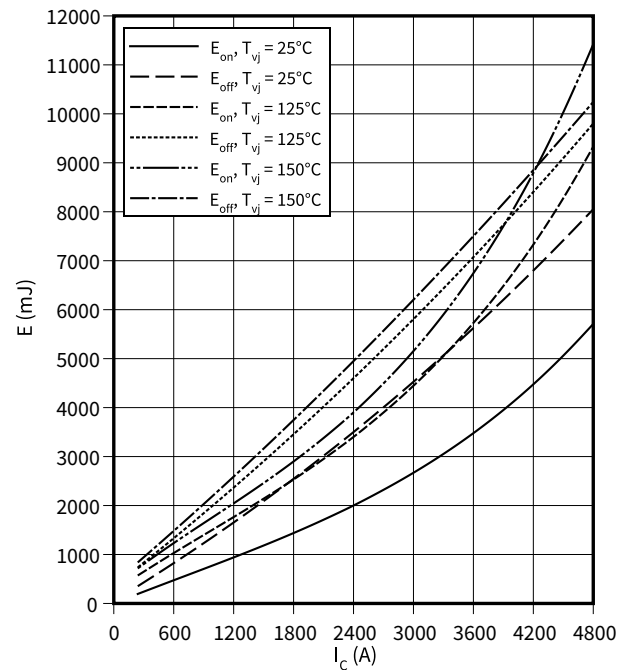
$$V_{CE} = 20 \text{ V}$$



switching losses (typical), IGBT, Inverter

$$E = f(I_C)$$

$$R_{Goff} = 3.3 \text{ } \Omega, R_{Gon} = 0.5 \text{ } \Omega, V_{CE} = 1800 \text{ V}, V_{GE} = \pm 15 \text{ V}$$

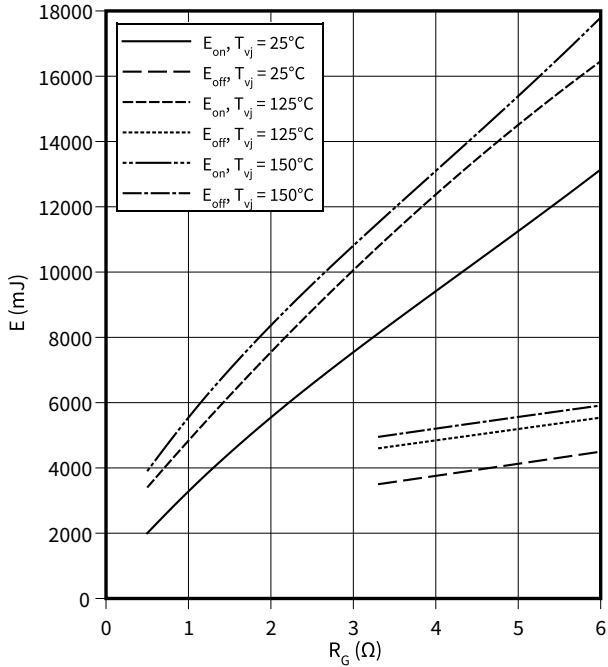


4 Characteristics diagrams

switching losses (typical), IGBT, Inverter

$E = f(R_G)$

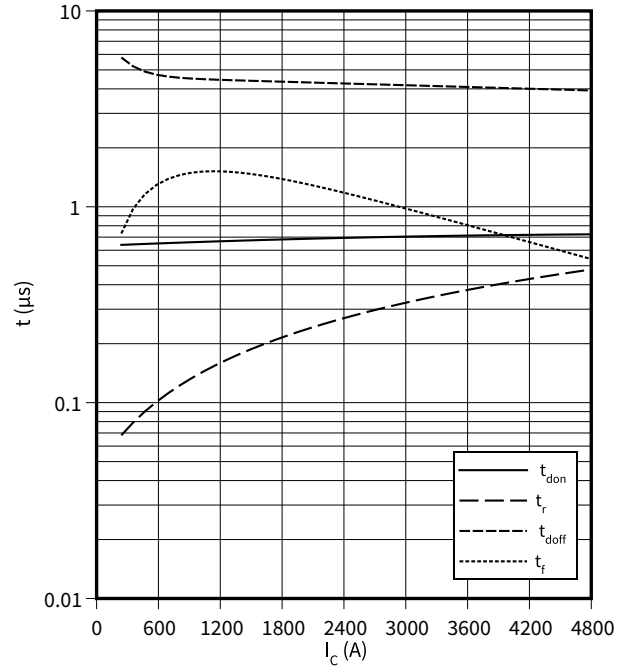
$I_C = 2400\text{ A}$, $V_{CE} = 1800\text{ V}$, $V_{GE} = \pm 15\text{ V}$



switching times (typical), IGBT, Inverter

$t = f(I_C)$

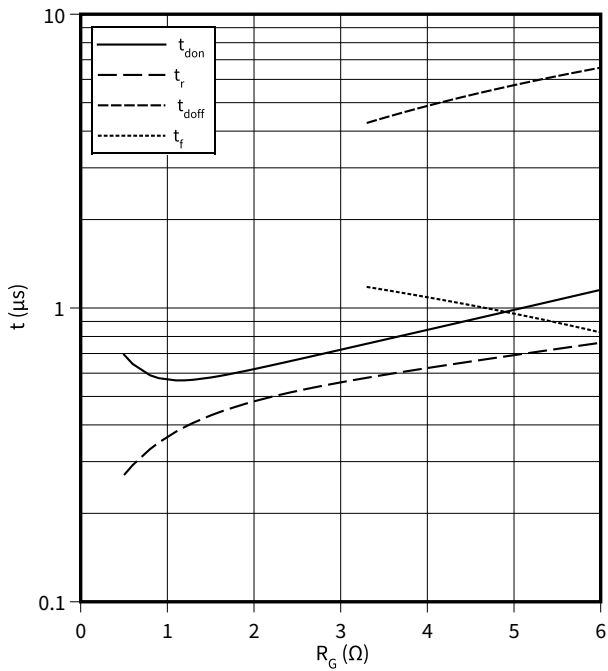
$R_{Goff} = 3.3\ \Omega$, $R_{Gon} = 0.5\ \Omega$, $V_{CE} = 1800\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 125\text{ °C}$



switching times (typical), IGBT, Inverter

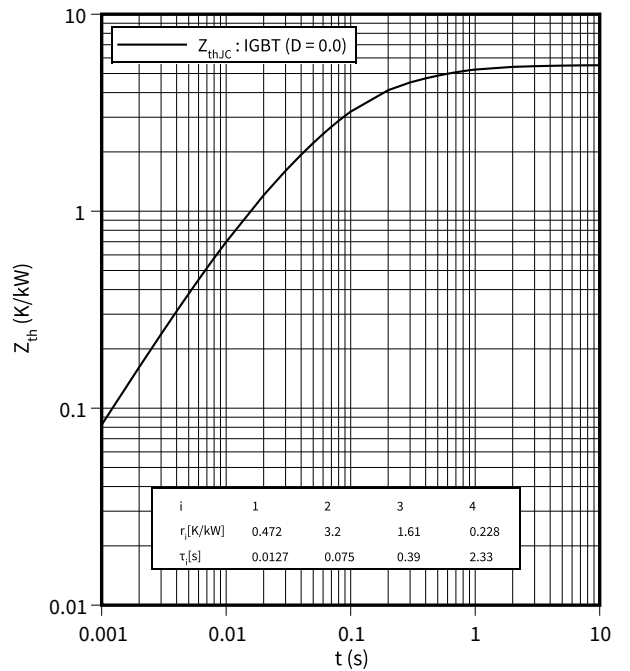
$t = f(R_G)$

$I_C = 2400\text{ A}$, $V_{CE} = 1800\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 125\text{ °C}$



transient thermal impedance, IGBT, Inverter

$Z_{th} = f(t)$

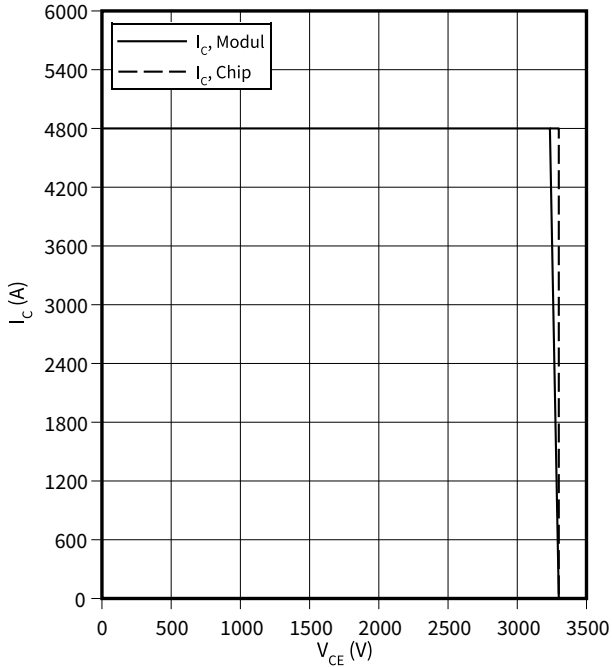


4 Characteristics diagrams

reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$

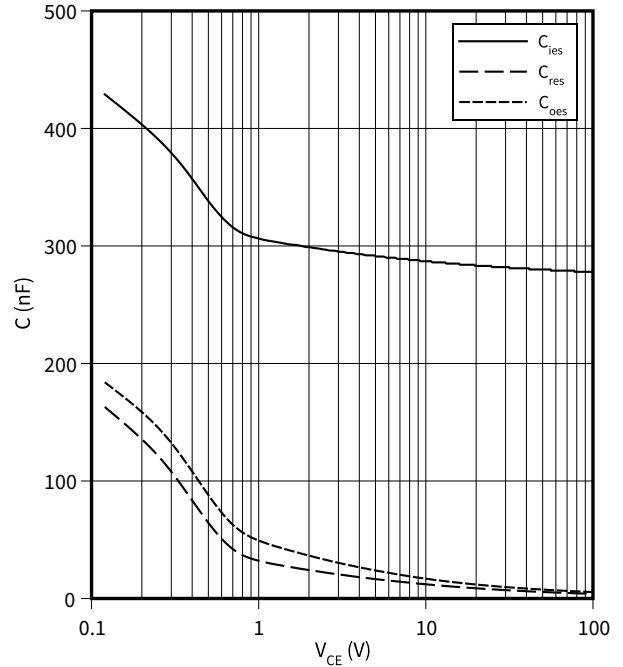
$R_{Goff} = 3.3 \Omega, V_{GE} = 15 V, T_{vj} = 150 \text{ }^\circ\text{C}$



capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

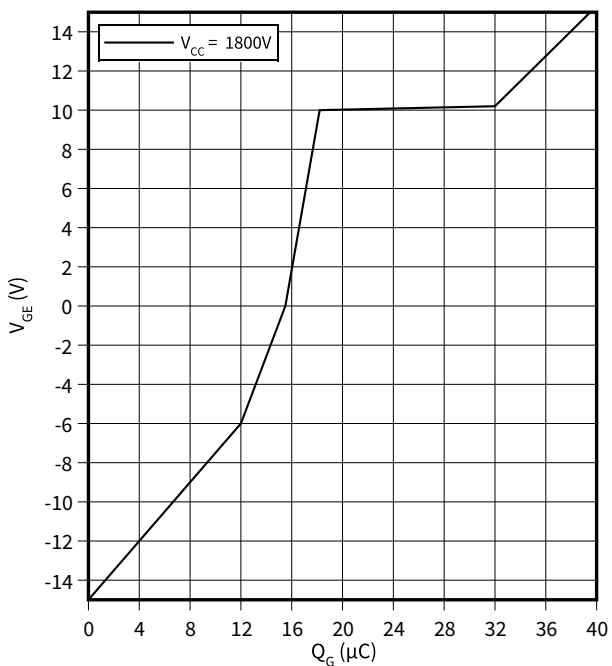
$f = 100 \text{ kHz}, V_{GE} = 0 V, T_{vj} = 25 \text{ }^\circ\text{C}$



gate charge characteristic (typical), IGBT, Inverter

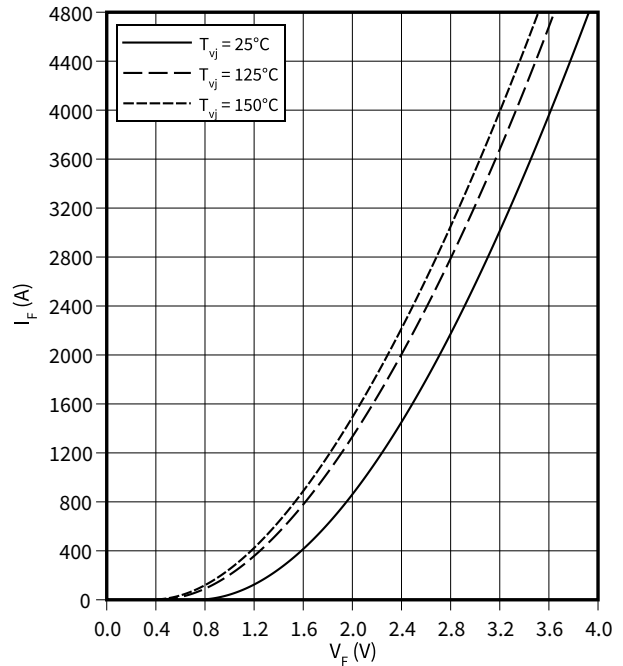
$V_{GE} = f(Q_G)$

$I_C = 2400 A, T_{vj} = 25 \text{ }^\circ\text{C}$



forward characteristic of (typical), Diode, Inverter

$I_F = f(V_F)$

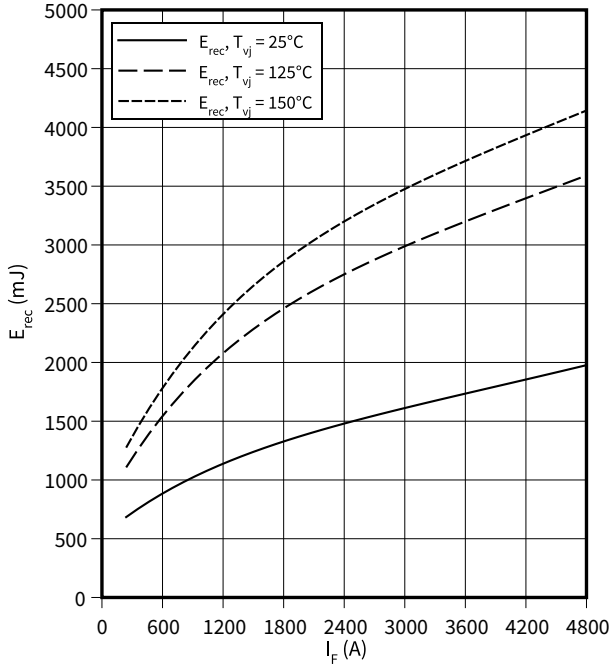


4 Characteristics diagrams

switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

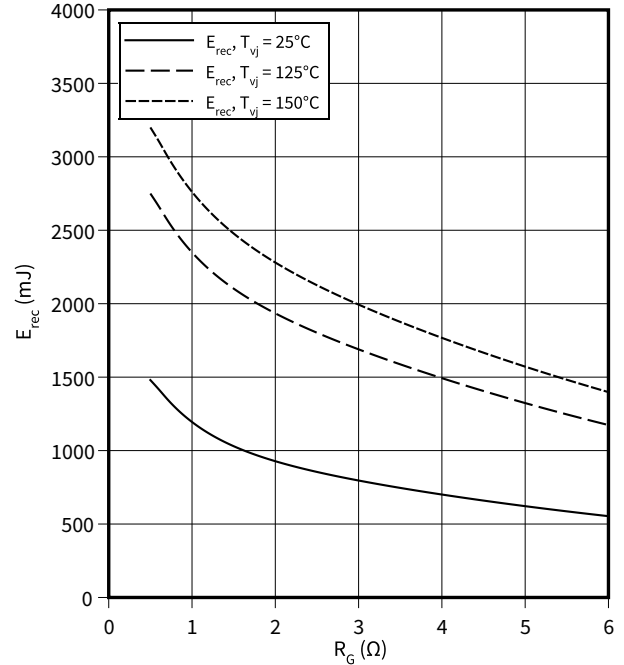
$V_{CE} = 1800\text{ V}$, $R_{Gon} = R_{Gon}(IGBT)$



switching losses (typical), Diode, Inverter

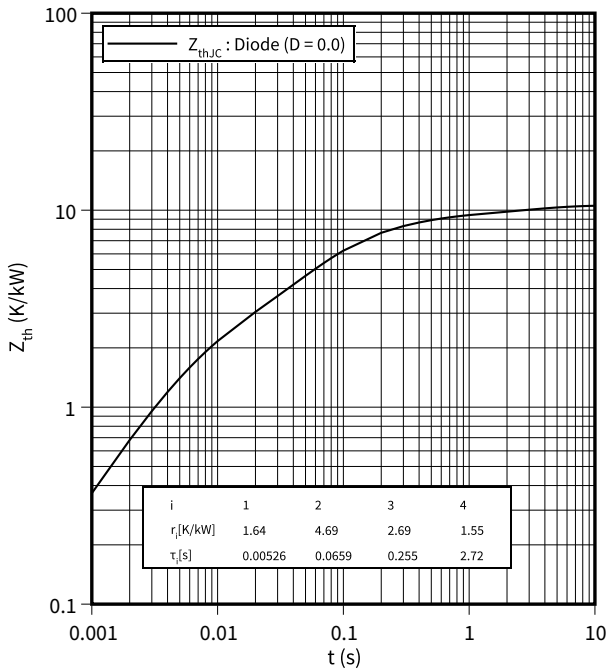
$E_{rec} = f(R_G)$

$V_{CE} = 1800\text{ V}$, $I_F = 2400\text{ A}$



transient thermal impedance , Diode, Inverter

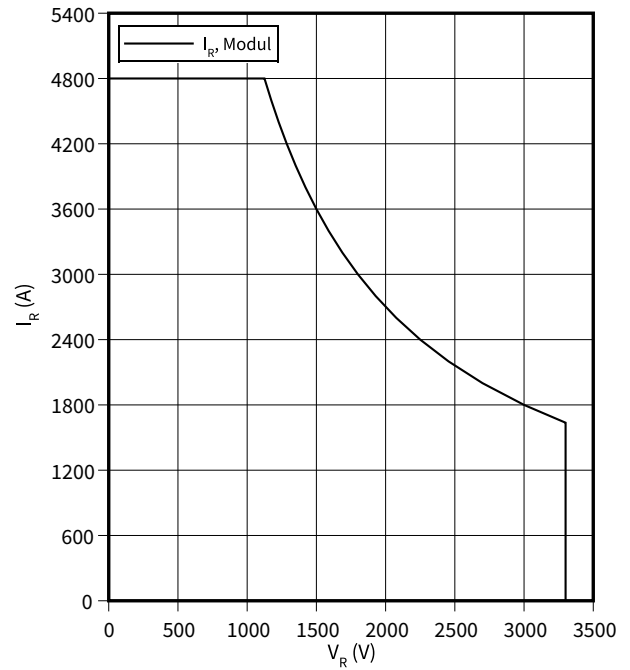
$Z_{th} = f(t)$



safe operation area (SOA), Diode, Inverter

$I_R = f(V_R)$

$T_{vj} = 150\text{ °C}$



5 Circuit diagram

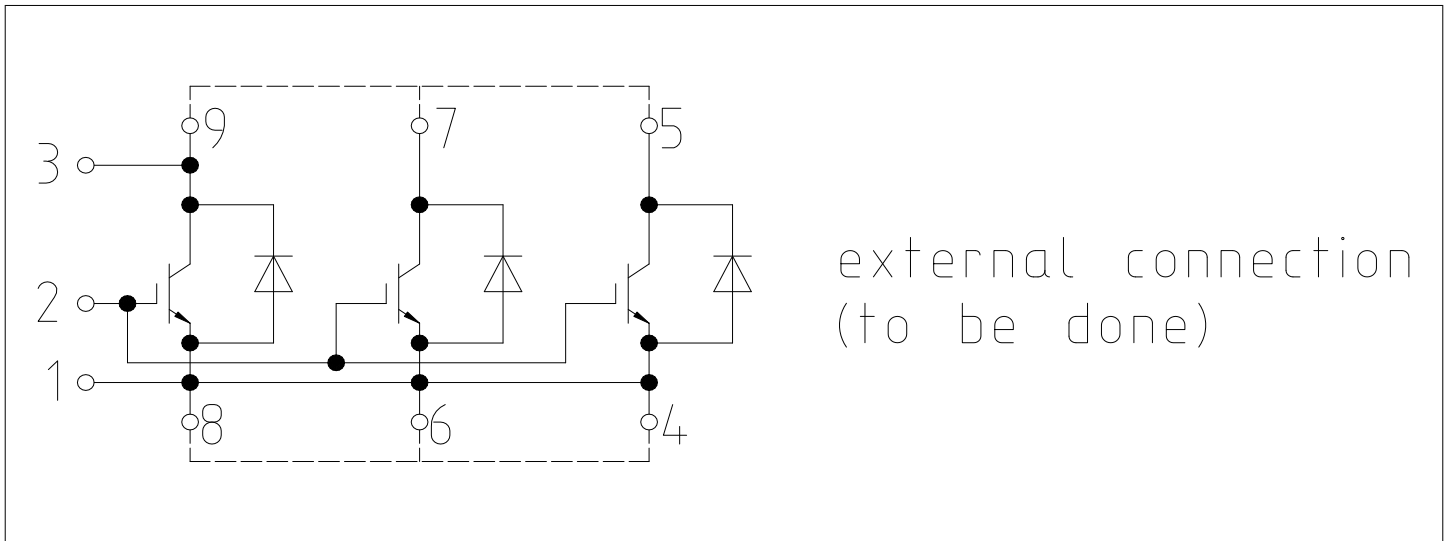


Figure 2

6 Package outlines

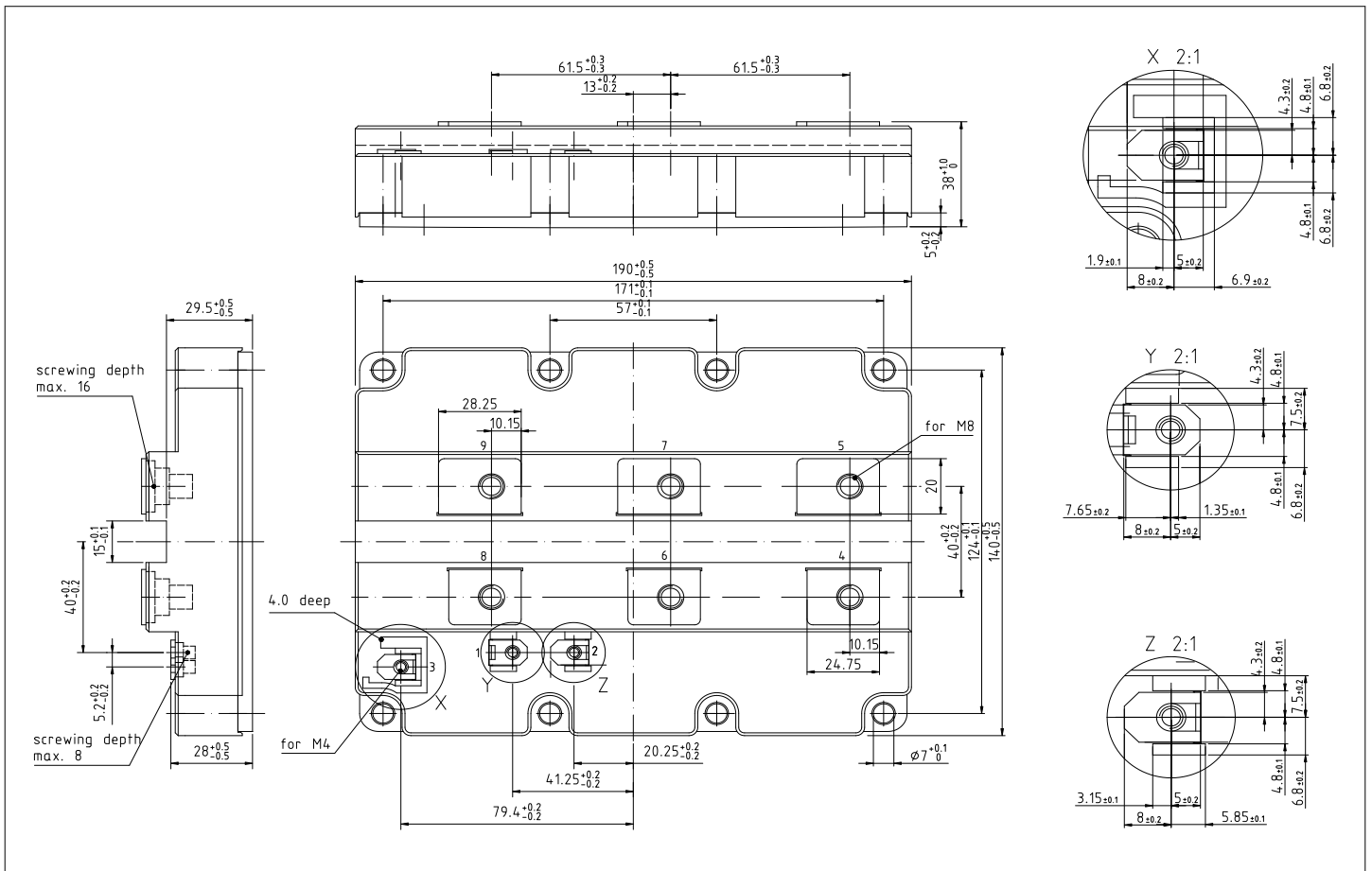


Figure 3

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